

Supplementary materials

Performance enhancement of solution-processed InZnO thin-film transistors by Al doping and surface passivation

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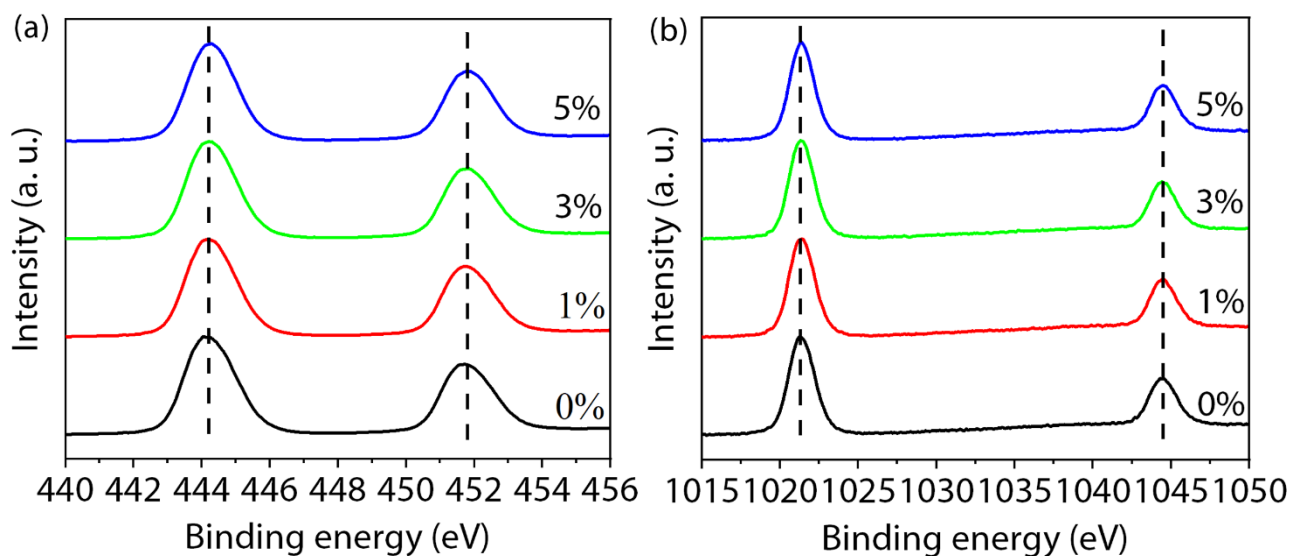


Fig. S1. XPS spectra of (a) In and (b) Zn peaks at different Al doping percentages.

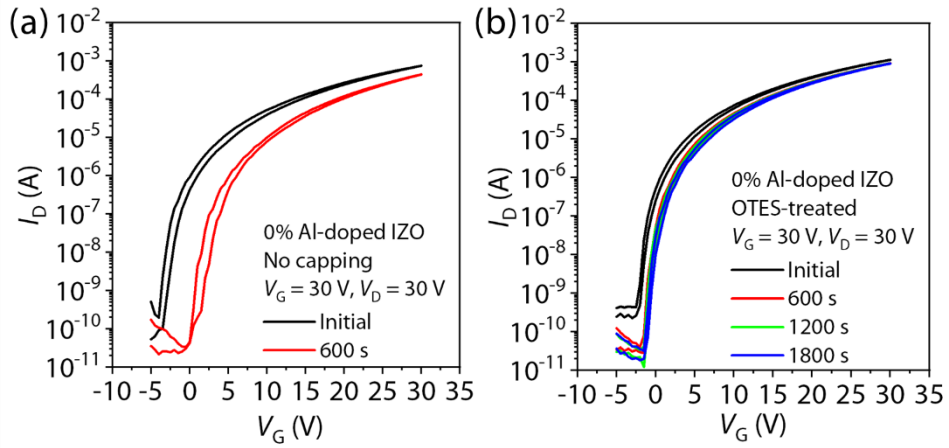


Fig. S2. Transfer characteristics of (a) untreated and (b) OTES-treated IZO TFTs under a PBS.

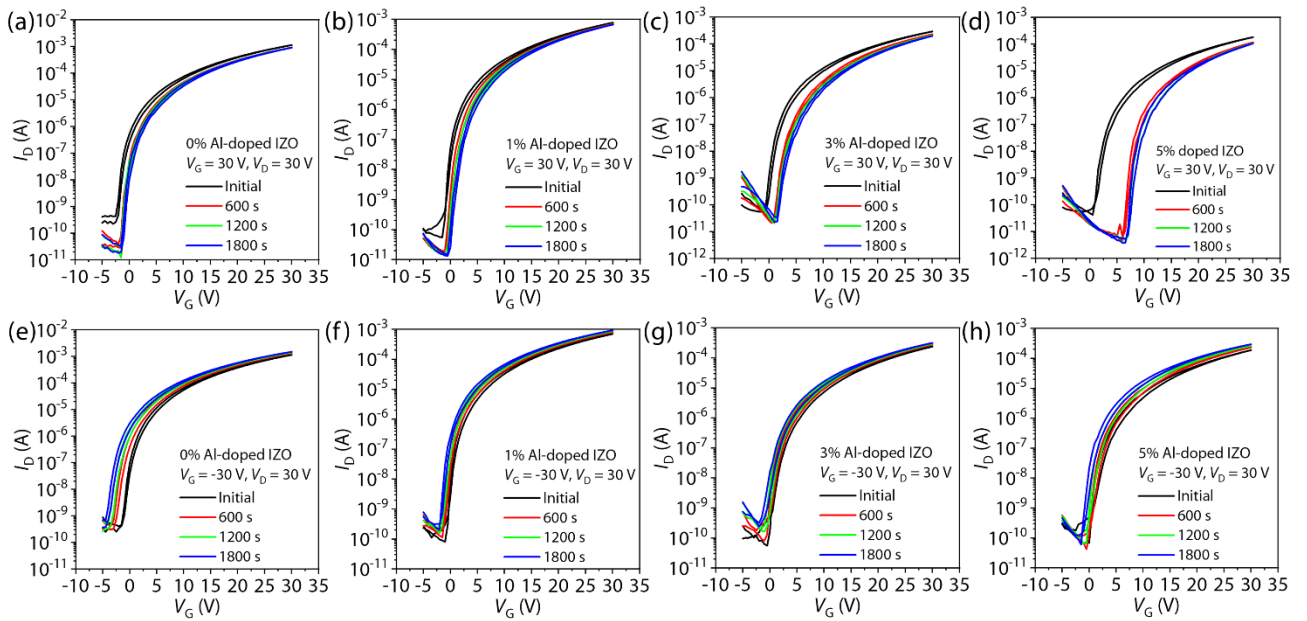


Fig. S3. Transfer characteristics of IZO:Al TFTs with different doping percentages under (a-d) a PBS of $V_G = 30$ V and (e-h) a NBS of $V_G = -30$ V for 1800 s.